L Number	Hits	Search Text	DB	Time stamp
-	157	semiconductor and plug and (antifuse)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/13 15:43
-	487	semiconductor and interconnect and (antifuse)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 12:08
-	205	(semiconductor and interconnect and (antifuse)) and (sidewall or barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:50
-	26	(semiconductor and interconnect and (antifuse)) and (SiN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:53
-	0	(semiconductor and interconnect and (antifuse)) and (silicon with nitrde)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:54
-	180	(semiconductor and interconnect and (antifuse)) and (silicon with nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:54
-	154	((semiconductor and interconnect and (antifuse)) and (silicon with nitride)) not ((semiconductor and interconnect and (antifuse)) and (SiN))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:54
-	40	(ESD with protection) and antifuse	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 15:43
-	1	(ESD with protection) and antifuse and trench$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 15:45
-	2	("6396120").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 15:50
-	13	("4476478" | "5166556" | "5250459" | "5304508" | "5314840" | "5469109" | "5485032" | "5572062" | "5672994" | "5774011" | "5804500" | "5811870" | "5904507").PN.	USPAT	2003/01/15 15:46
-	2	("6458631").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 15:51
-	2	("6440850").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 15:55
-	2	("6335228").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 15:55

–	6	("5904507" | "6081021" | "6087677" | "6097077" | "6124194" | "6335228").PN.	USPAT	2003/01/15 16:22
–	5	semiconductor and antifuse and BPSG and "p-type" and "n-type" and (doped with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 10:13
–	9	semiconductor and antifuse and BPSG and "p-type" and "n-type"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 10:13
–	4	(semiconductor and antifuse and BPSG and "p-type" and "n-type") not (semiconductor and antifuse and BPSG and "p-type" and "n-type" and (doped with silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 10:42
–	2817	semiconductor and plug$1 and "p-type" and "n-type"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 10:43
–	767	(semiconductor and plug$1 and "p-type" and "n-type") and BPSG	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 10:43
–	267	((semiconductor and plug$1 and "p-type" and "n-type") and BPSG) and (copper or Cu)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 14:02
–	154	semiconductor and antifuse and "p-type" and "n-type"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 14:56
–	73	semiconductor and antifuse and BPSG	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 15:03
–	203	semiconductor and antifuse and (copper or cu)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 15:04
–	66	(semiconductor and antifuse and (copper or cu)) and (doped with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 15:17
–	52	semiconductor and plug and (barrier with SiON)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 15:23
–	1	(semiconductor and plug and (barrier with SiON)) and (doped with silicon with plug)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 15:24
–	2	(semiconductor and plug and (barrier with SiON)) and (doped with silicon with conductive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/21 15:24